

**General Description**

The ZM140N10D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Features

Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

Application

nd Synchronous Rectifier

Product Summary**Ordering Information:**

Part NO.	ZM140N10D
Marking	ZM140N10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

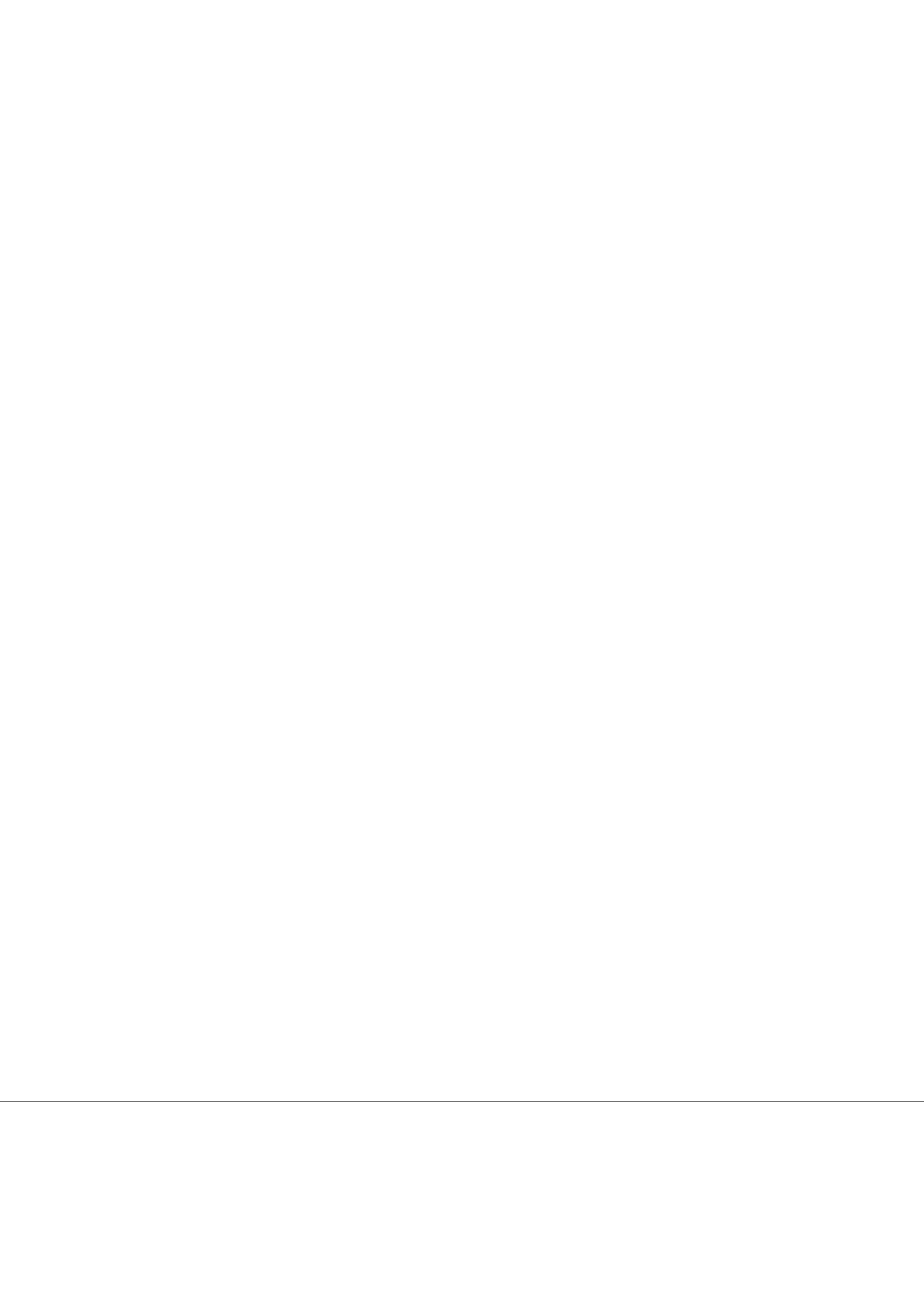
Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	40	A
	$I_{D@TC=75}$	30.4	A
	$I_{D@TC=100}$	25.2	A
Pulsed Drain Current	I_{DM}	100	A
Total Power Dissipation($TC=25$)	$P_D@TC=25$	70	W
Total Power Dissipation($TA=25$)	$P_D@TA=25$	2.8	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@ $L=0.1mH$	E_{AS}	80	mJ
Avalanche Current@ $L=0.1mH$	I_{AS}	40	A



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.8	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	45	° C/W





ZM140N10D

100V N-Channel Power MOSFET
